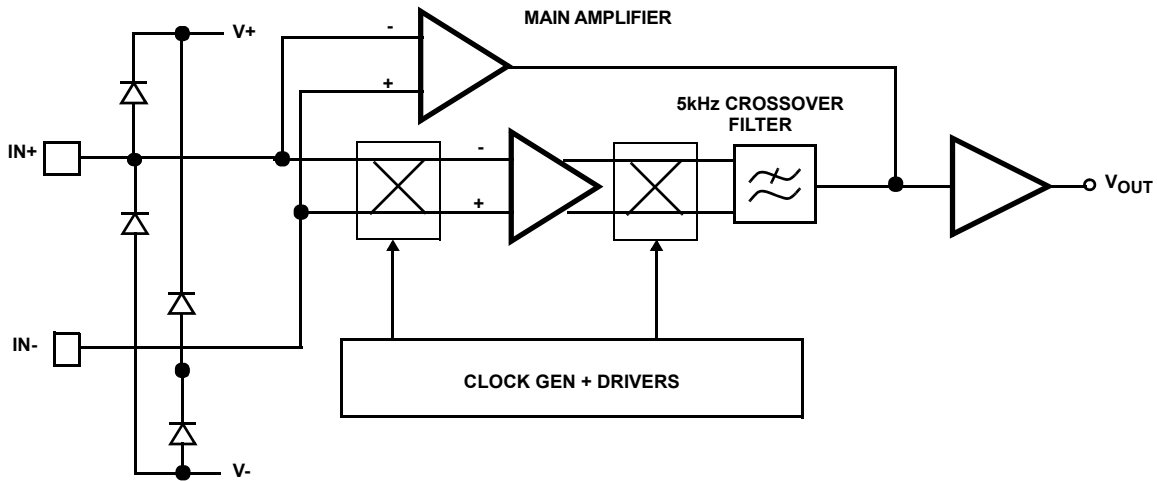


Block Diagram



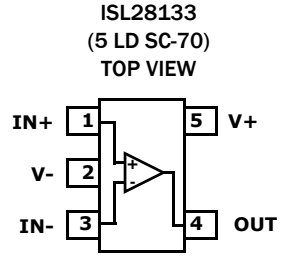
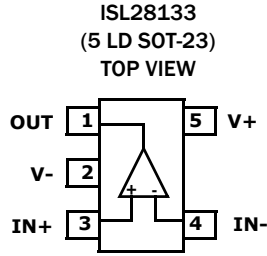
Ordering Information

PART NUMBER	PART MARKING	PACKAGE DESCRIPTION (RoHS Compliant)	PKG. DWG. #	CARRIER TYPE (Note 1)
ISL28133FHZ-T7 (Note 2)	BCFA (Note 5)	5 Ld SOT-23	P5.064A	Reel, 3k
ISL28133FHZ-T7A (Note 2)				Reel, 250
ISL28133FEZ-T7 (Note 2)	BHA (Note 5)	5 Ld SC70	P5.049	Reel, 3k
ISL28133ISENSEV1Z	Evaluation Board			
ISL28133EVAL1Z	Evaluation Board			
ISL28133CSENSEV1Z	Evaluation Board			

NOTES:

- See [TB347](#) for details on reel specifications.
- These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- These Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- For Moisture Sensitivity Level (MSL), please see the device information page for the [ISL28133](#). For more information on MSL please see techbrief [TB363](#).
- The part marking is located on the bottom of the part.

Pin Configurations



TOP VIEW

Pin Descriptions

ISL28133 (5 Ld SOT23)	ISL28133 (5 Ld SC-70)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	1	IN+	Non-inverting input	<p>Circuit 1</p>
2	2	V-	Negative supply	
4	3	IN-	Inverting input	(See Circuit 1)
1	4	OUT	Output	<p>Circuit 2</p>
5	5	V+	Positive supply	

Absolute Maximum Ratings

Max Supply Voltage V+ to V-	6.5V
Max Voltage VIN to GND	-0.5V to 6.5V
Max Input Differential Voltage	6.5V
Max Input Current	20mA
Max Voltage VOUT to GND (10s)	6.5V
ESD Rating	
Human Body Model	3000V
Machine Model	200V
Charged Device Model	1500V

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
5 Ld SOT-23 (Note 6, 7)	225	110
5 Ld SC-70 (Note 6)	206	N/A
Maximum Storage Temperature Range	-65°C to +150°C	
Pb-Free Reflow Profile	see TB493	

Operating Conditions

Temperature Range	-40°C to +125°C
Maximum Junction Temperature	140°C

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

- θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air. See [TB379](#) for details.
- For θ_{JC} , the "case temp" location is taken at the package top center.

Electrical Specifications $V_+ = 5V$, $V_- = 0V$, $V_{CM} = 2.5V$, $T_A = +25^\circ C$, $R_L = \text{Open}$, unless otherwise specified. **Boldface limits apply over the operating temperature range, -40°C to +125°C.**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 8)	TYP	MAX (Note 8)	UNIT
DC SPECIFICATIONS						
V _{OS}	Input Offset Voltage		-8	±2	8	μV
			-15.5		15.5	μV
TCV _{OS}	Input Offset Voltage Temperature Coefficient			0.02	0.075	μV/°C
I _{OS}	Input Offset Current			-60		pA
I _B	Input Bias Current		-300	±30	300	pA
			-600		600	pA
Common Mode Input Voltage Range		V+ = 5.0V, V- = GND	-0.1		5.1	V
CMRR	Common Mode Rejection Ratio	V _{CM} = -0.1V to 5.0V	118	125		dB
			115			dB
PSRR	Power Supply Rejection Ratio	V _s = 2V to 5.5V	110	138		dB
			110			dB
V _{OH}	Output Voltage Swing, High	R _L = 10kΩ	4.965	4.981		V
V _{OL}	Output Voltage Swing, Low	R _L = 10kΩ		18	35	mV
A _{OL}	Open Loop Gain	R _L = 1MΩ		174		dB
V+	Supply Voltage	(Note 9)	1.8		5.5	V
I _S	Supply Current	R _L = OPEN		18	25	μA
					35	μA
I _{SC+}	Output Source Short Circuit Current	R _L = Short to ground or V+	13	17	26	mA
I _{SC-}	Output Sink Short Circuit Current		-26	-19	-13	mA
AC SPECIFICATIONS						
GBWP	Gain Bandwidth Product f = 50kHz	A _V = 100, R _F = 100kΩ, R _G = 1kΩ, R _L = 10kΩ to V _{CM}		400		kHz
e _N V _{P-P}	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz		1.1		μV _{P-P}
e _N	Input Noise Voltage Density	f = 1kHz		65		nV/√(Hz)

Electrical Specifications $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, T_A = +25^\circ C, R_L = \text{Open}$, unless otherwise specified. **Boldface limits apply over the operating temperature range, $-40^\circ C$ to $+125^\circ C$. (Continued)**

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 8)	TYP	MAX (Note 8)	UNIT
i_N	Input Noise Current Density	$f = 1\text{kHz}$		72		$fA/\sqrt{\text{Hz}}$
		$f = 10\text{Hz}$		79		$fA/\sqrt{\text{Hz}}$
C_{in}	Differential Input Capacitance	$f = 1\text{MHz}$		1.6		pF
	Common Mode Input Capacitance			1.12		pF
TRANSIENT RESPONSE						
SR	Positive Slew Rate	$V_{OUT} = 1V \text{ to } 4V, R_L = 10k\Omega$		0.2		$V/\mu s$
	Negative Slew Rate			0.1		$V/\mu s$
t_r, t_f , Small Signal	Rise Time, t_r 10% to 90%	$A_V = +1, V_{OUT} = 0.1V_{P-P}, R_F = 0\Omega, R_L = 10k\Omega, C_L = 1.2pF$		1.1		μs
	Fall Time, t_f 10% to 90%			1.1		μs
t_r, t_f Large Signal	Rise Time, t_r 10% to 90%	$A_V = +1, V_{OUT} = 2V_{P-P}, R_F = 0\Omega, R_L = 10k\Omega, C_L = 1.2pF$		8		μs
	Fall Time, t_f 10% to 90%			10		μs
t_s	Settling Time to 0.1%, $2V_{P-P}$ Step	$A_V = +1, R_F = 0\Omega, R_L = 10k\Omega, C_L = 1.2pF$		35		μs

NOTES:

- 8. Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design.
- 9. Parts are 100% tested with a minimum operating voltage of 1.8V to a VOS limit of $\pm 15\mu V$.

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open}$.

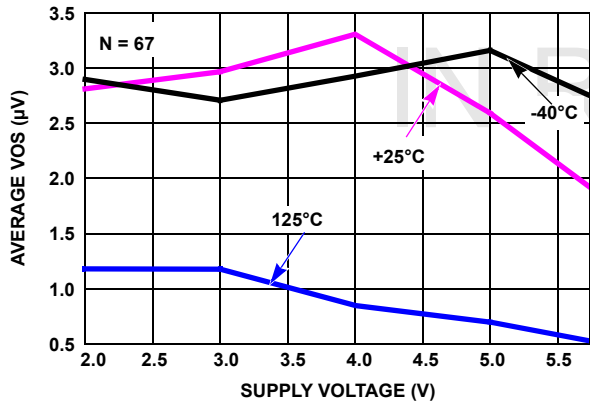


FIGURE 3. AVERAGE INPUT OFFSET VOLTAGE vs SUPPLY VOLTAGE

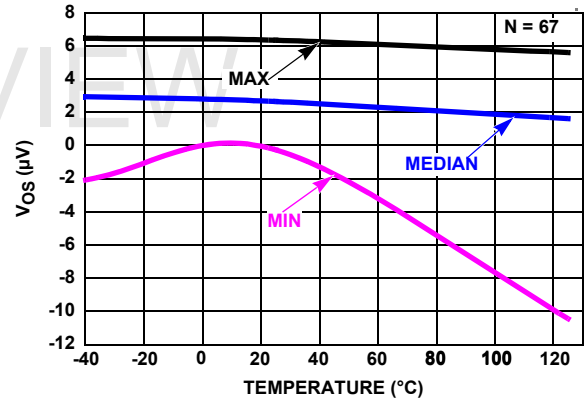


FIGURE 4. V_{OS} vs TEMPERATURE, $V_S = \pm 1.0V, V_{IN} = 0V, R_L = \text{INF}$

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open. (Continued)}$

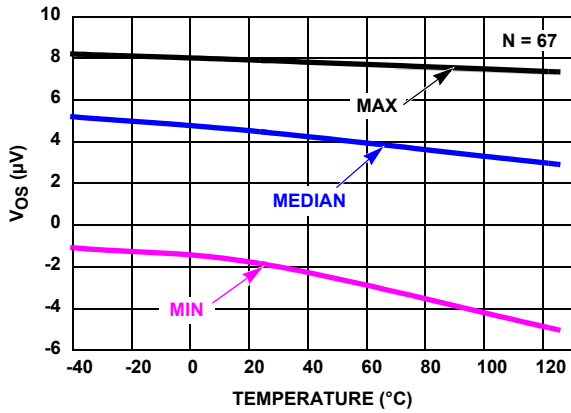


FIGURE 5. V_{OS} vs TEMPERATURE, $V_S = \pm 2.5V, V_{IN} = 0V, R_L = \text{INF}$

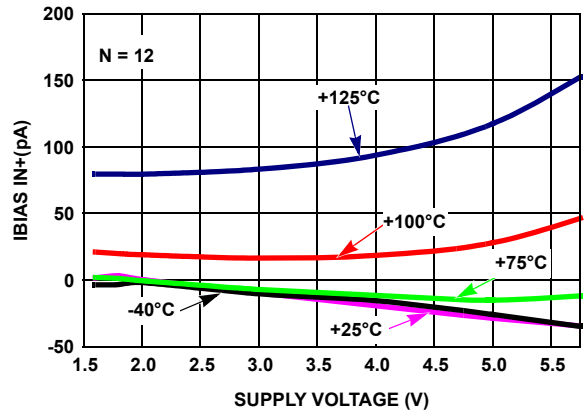


FIGURE 6. I_{B+} vs SUPPLY VOLTAGE vs TEMPERATURE

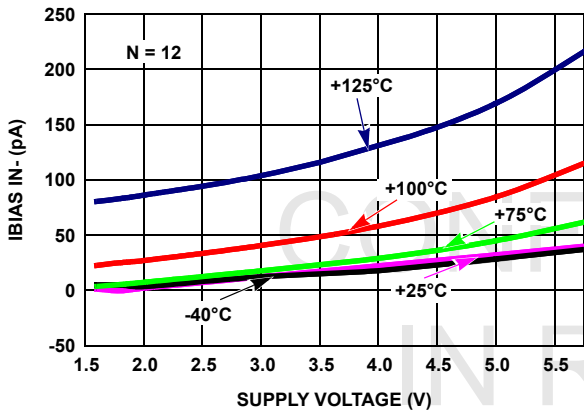


FIGURE 7. I_{B-} vs SUPPLY VOLTAGE vs TEMPERATURE

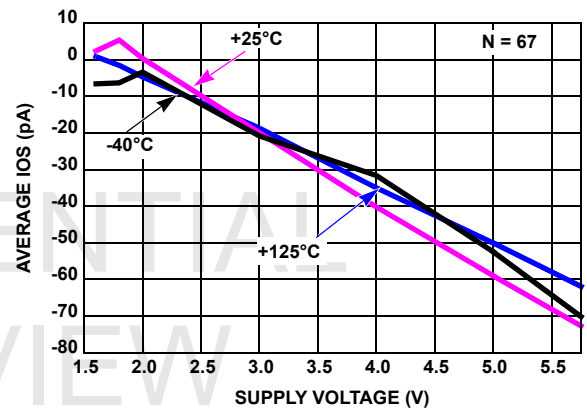


FIGURE 8. I_{OS} vs SUPPLY VOLTAGE vs TEMPERATURE

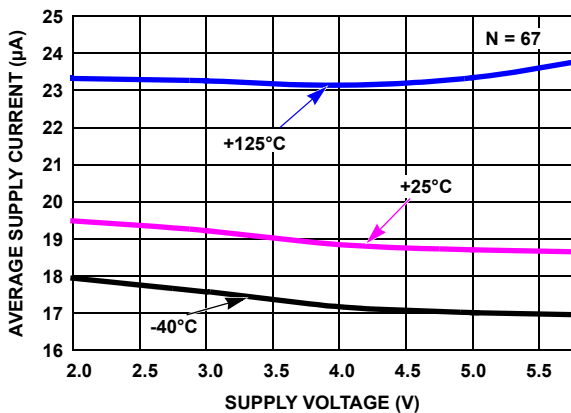


FIGURE 9. AVERAGE SUPPLY CURRENT vs SUPPLY VOLTAGE

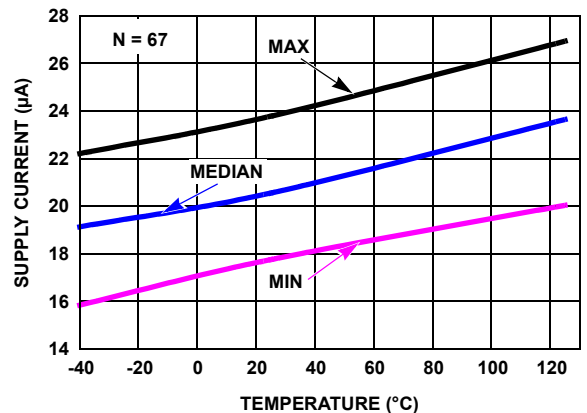


FIGURE 10. MIN/MAX SUPPLY CURRENT vs TEMPERATURE, $V_S = \pm 0.8V, V_{IN} = 0V, R_L = \text{INF}$

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open}$. (Continued)

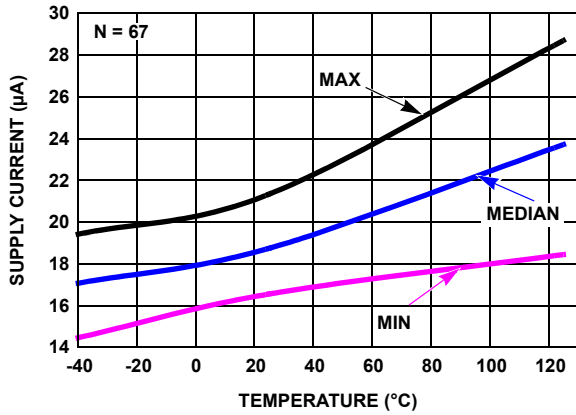


FIGURE 11. MIN/MAX SUPPLY CURRENT vs TEMPERATURE,
 $V_S = \pm 2.5V, V_{IN} = 0V, R_L = \text{INF}$

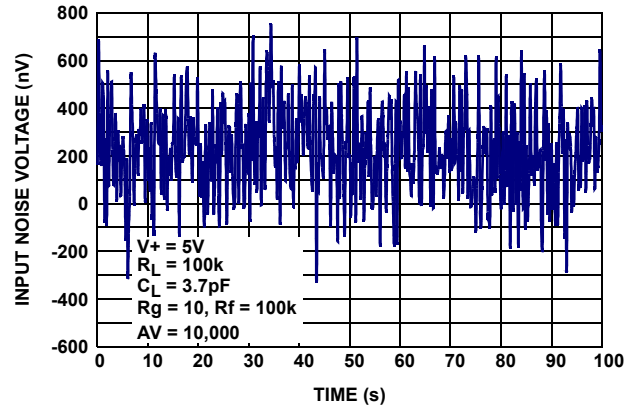


FIGURE 12. INPUT NOISE VOLTAGE 0.01Hz TO 10Hz

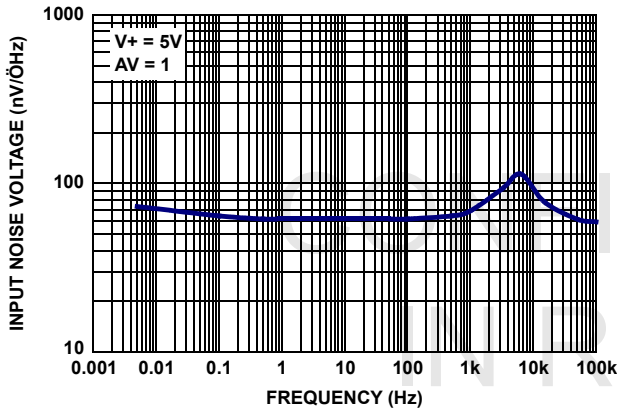


FIGURE 13. INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

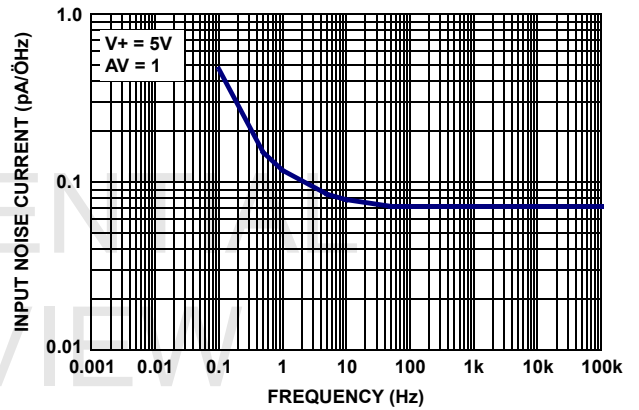


FIGURE 14. INPUT NOISE CURRENT DENSITY vs FREQUENCY

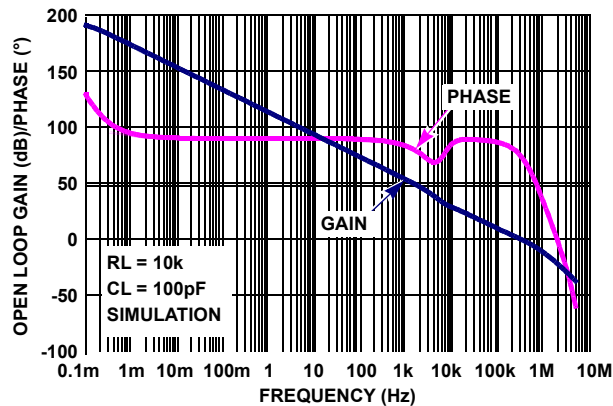


FIGURE 15. FREQUENCY RESPONSE vs OPEN LOOP GAIN, $R_L = 10k$

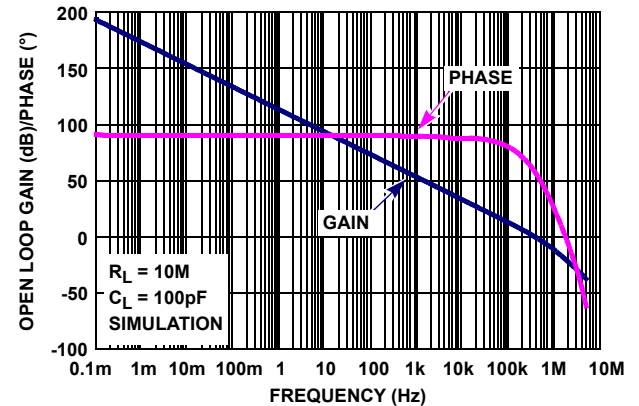


FIGURE 16. FREQUENCY RESPONSE vs OPEN LOOP GAIN, $R_L = 10M$

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open}$. (Continued)

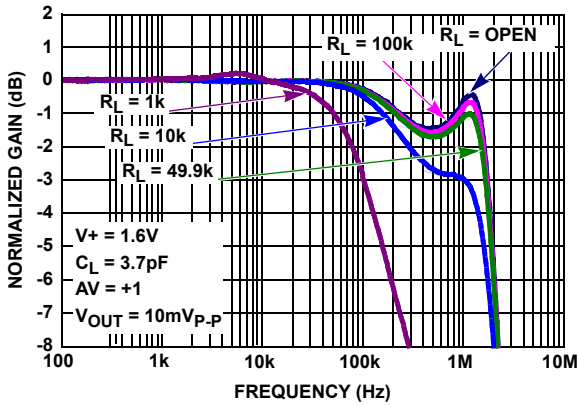


FIGURE 17. GAIN vs FREQUENCY vs $R_L, V_S = 1.6V$

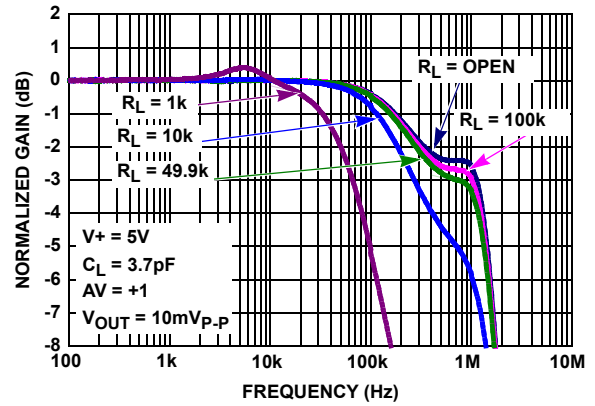


FIGURE 18. GAIN vs FREQUENCY vs $R_L, V_S = 5V$

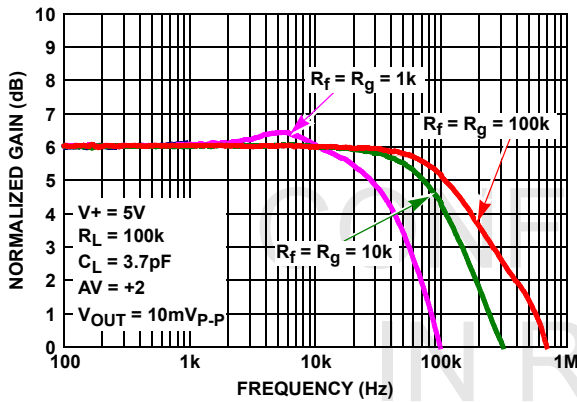


FIGURE 19. GAIN vs FREQUENCY vs FEEDBACK RESISTOR VALUES R_f/R_g

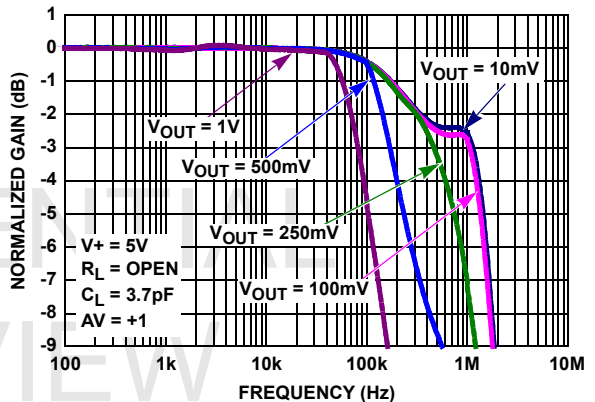


FIGURE 20. GAIN vs FREQUENCY vs $V_{OUT}, R_L = \text{OPEN}$

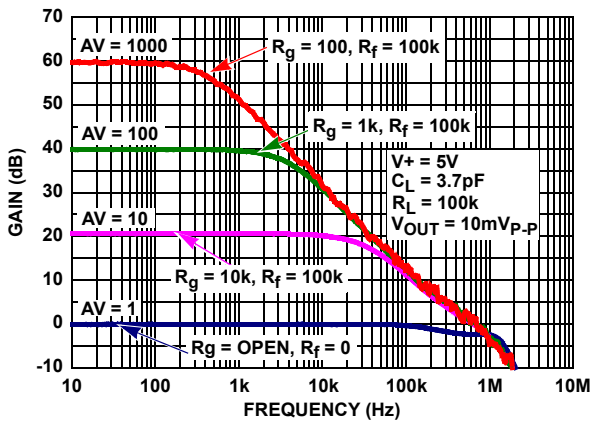


FIGURE 21. FREQUENCY RESPONSE vs CLOSED LOOP GAIN

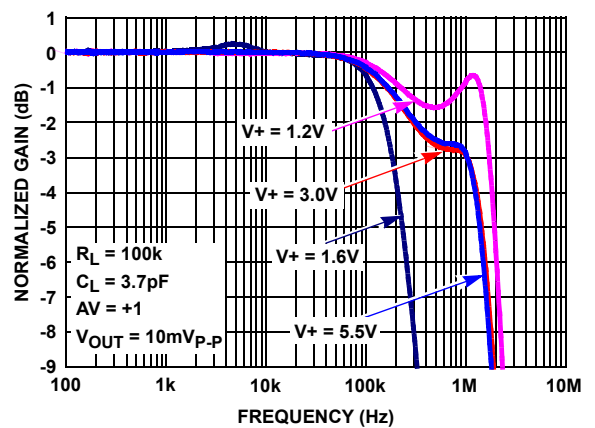


FIGURE 22. GAIN vs FREQUENCY vs SUPPLY VOLTAGE

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open}$. (Continued)

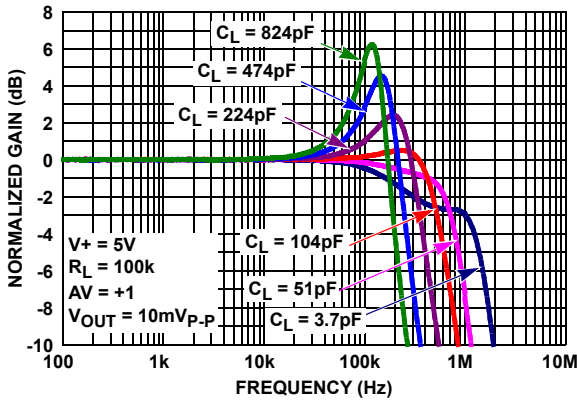


FIGURE 23. GAIN vs FREQUENCY vs C_L

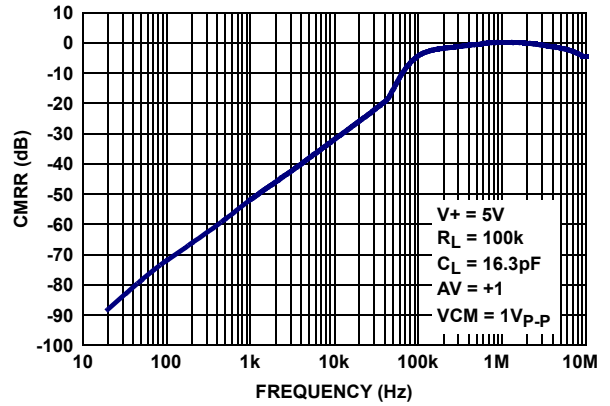


FIGURE 24. CMRR vs FREQUENCY, $V_S = 5V$

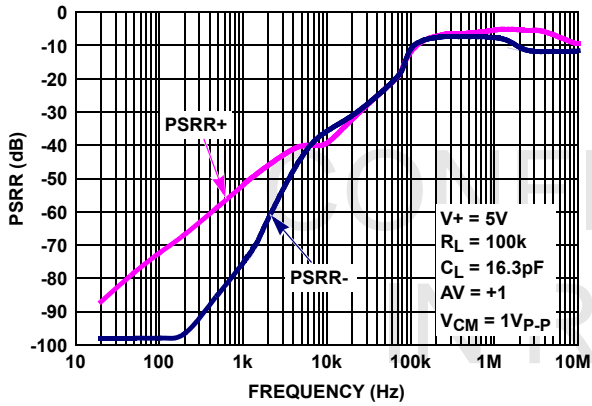


FIGURE 25. PSRR vs FREQUENCY, $V_S = 5V$

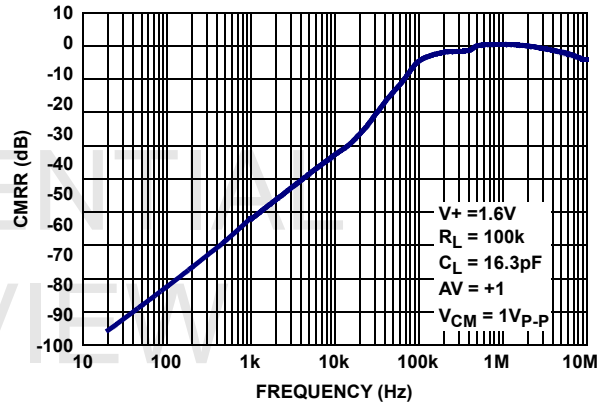


FIGURE 26. CMRR vs FREQUENCY, $V_S = 1.6V$

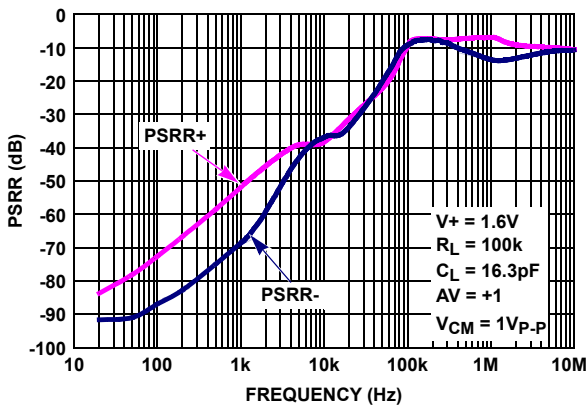


FIGURE 27. PSRR vs FREQUENCY, $V_S = 1.6V$

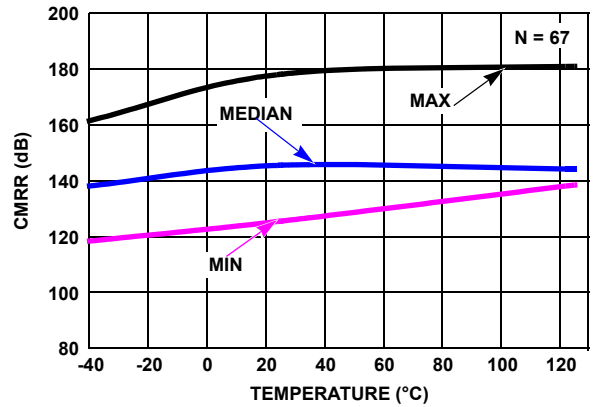


FIGURE 28. CMRR vs TEMPERATURE, $V_{CM} = -2.5V \text{ TO } +2.5V, V_+ = \pm 2.5V$

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open}$. (Continued)

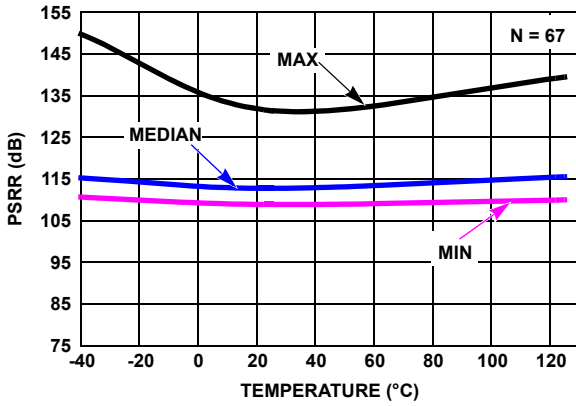


FIGURE 29. PSRR vs TEMPERATURE, $V_+ = 2V$ TO $5.5V$

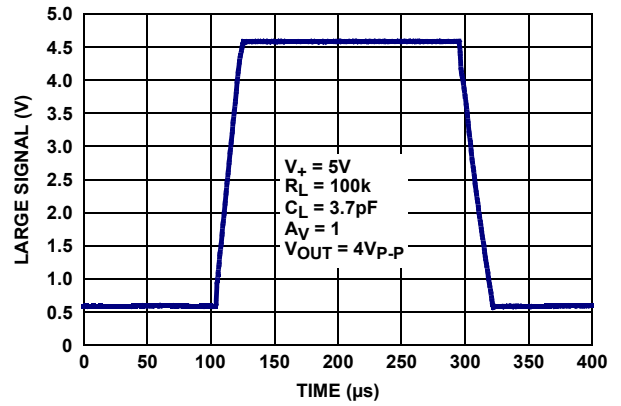


FIGURE 30. LARGE SIGNAL STEP RESPONSE (4V)

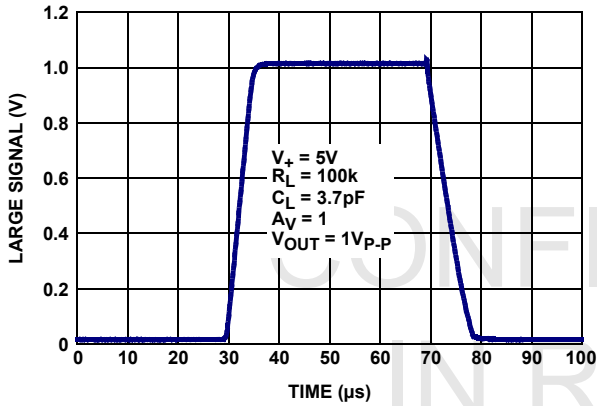


FIGURE 31. LARGE SIGNAL STEP RESPONSE (1V)

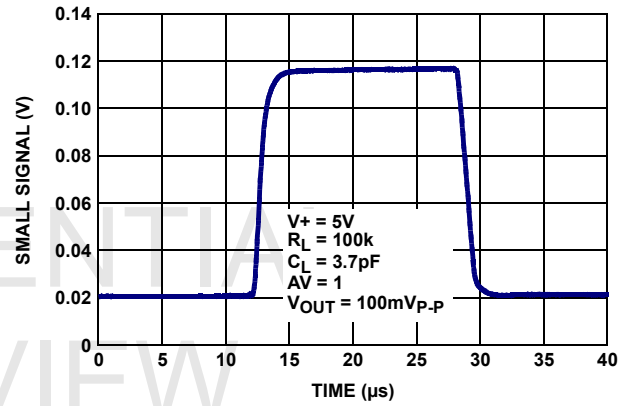


FIGURE 32. SMALL SIGNAL STEP RESPONSE (100mV)

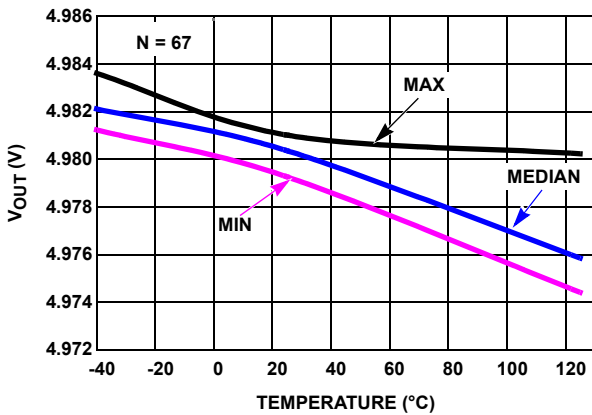


FIGURE 33. V_{OUT} HIGH vs TEMPERATURE, $R_L = 10k, V_S = 5V$

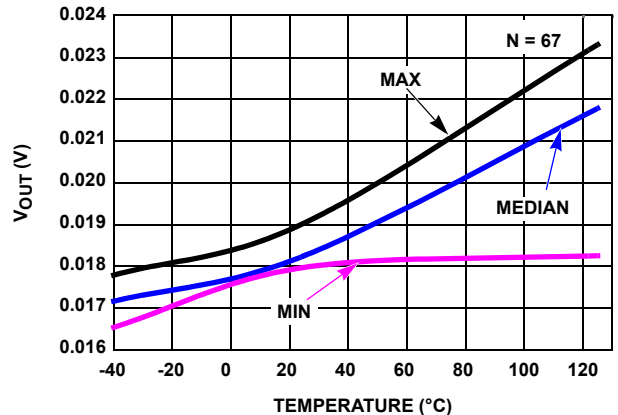


FIGURE 34. V_{OUT} LOW vs TEMPERATURE, $R_L = 10k, V_S = 5V$

Typical Performance Curves $V_+ = 5V, V_- = 0V, V_{CM} = 2.5V, R_L = \text{Open. (Continued)}$

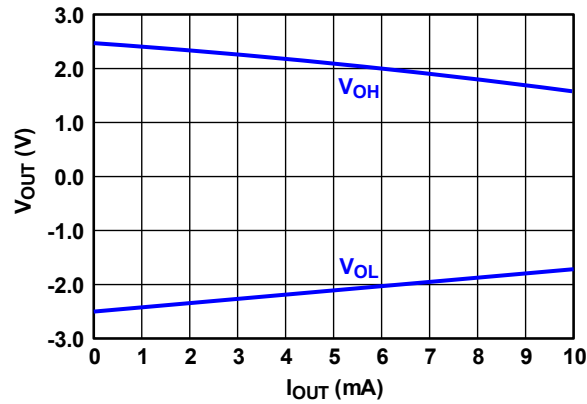


FIGURE 35. V_{OH}, V_{OL} vs I_{OUT} , $V_S = \pm 2.5V$

Applications Information

Functional Description

The ISL28133 uses a proprietary chopper-stabilized architecture shown in the “Block Diagram” on page 2. The ISL28133 combines a 400kHz main amplifier with a very high open loop gain (174dB) chopper stabilized amplifier to achieve very low offset voltage and drift ($2\mu V, 0.02\mu V/^\circ C$ typical) while consuming only $18\mu A$ of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallel-connected, high gain chopper stabilized DC correction amplifier operating at 100kHz. From DC to $\sim 5kHz$, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A 5kHz crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the 400kHz gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low $1/f$ noise. The noise is virtually flat across the frequency range from a few mHz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

Rail-to-rail Input and Output (RRIO)

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a $10k\Omega$ load.

IN+ and IN- Protection

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (see Figure 36).

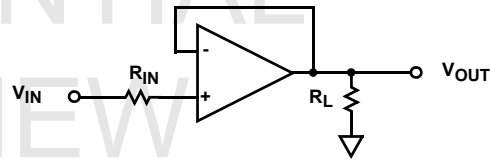


FIGURE 36. INPUT CURRENT LIMITING

Layout Guidelines for High Impedance Inputs

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28133 amplifiers, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board.

High Gain, Precision DC-Coupled Amplifier

The circuit in Figure 37 implements a single-stage, $10kV/V$ DC-coupled amplifier with an input DC sensitivity of under $100nV$ that is only possible using a low V_{OS} amplifier with high open loop gain. This circuit is practical down to 1.8V due to its rail-to-rail input and output capability. Standard high gain DC amplifiers operating from low voltage supplies are not practical at these high gains using typical low offset precision op amps because the input offset voltage and temperature coefficient consume most of the available output voltage swing. For example, a typical precision amplifier in a gain of $10kV/V$ with a $\pm 100\mu V$ V_{OS} and a temperature coefficient of $0.5\mu V/^\circ C$ would produce a DC error at the output of $>1V$ with an additional $5mV/^\circ C$ of temperature dependent error. At 3V, this DC error

